## EE539: Analog Integrated Circuit Design; Lecture 11

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## **Single Transistor Amplifiers**

- MOSFET a voltage controlled current source. By passing the current through a resistor, voltage gain can be obtained
- Transconductance  $(g_m)$  is higher in saturation region when compared to triode region Saturation:  $g_m = \frac{\mu C_{ox} W}{L} (V_{GS} - V_T)$ Triode:  $g_m = \frac{\mu C_{ox} W}{L} V_{DS}$  where  $V_{DS} < (V_{GS} - V_T)$
- Transconductance is almost independent of  $V_{DS}$  in the saturation region(there is a slight variation due to channel length modulation)

So, amplifiers are always biased in saturation region to get good amplification

## **Common Source Amplifier**

Small signal analysis-DC

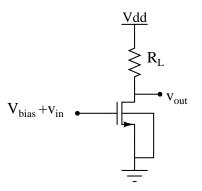


Figure 1: Common source amplifier

Assume that  $V_{dd}$  and  $V_{bias}$  bias the MOSFET in saturation.

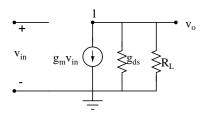


Figure 2: Small signal model at DC

Writing KCL at node 1,

 $V_{out}(g_{ds} + G_L) = -g_m V_{in}$   $\frac{V_{out}}{V_{in}} = -\frac{g_m}{g_{ds} + G_L} \approx -\frac{g_m}{G_L} \text{ if } g_{ds} << G_L$ Max DC gain =  $-\frac{g_m}{g_{ds}} (\text{at } R_L = \infty)$ Noting that  $g_m = \sqrt[S_{as}]{2\mu I_d C_{ox} \frac{W}{L}}$  and  $g_{ds} = \lambda I_d$ Max DC gain =  $\frac{\sqrt{2\mu C_{ox} \frac{W}{L}}}{\lambda} \frac{1}{\sqrt{I_d}}$ 

We see that, to get the highest possible DC gain,

- Bias current should be as low as possible
- Width of the transistor can be increased while keeping the bias current constant
- Length of the transistor can be increased while keeping the bias current constant. This stems from the fact that  $\lambda$  is inversely proportional to length

We also see from the small signal model that

 $R_{in} = \infty$  $R_{out} = \frac{1}{g_{ds} + G_L}$ 

## Small signal analysis-AC (qualitative)

Fig. 3 shows the small signal model at high frequencies. If  $C_{gd}$  is neglected, then

Gain= $-\frac{g_m}{g_{ds}+G_L+SC_{db}}$ There will be one pole at  $\frac{g_{ds}+G_L}{C_{db}}$ 

We also note that as  $R_L$  increases, gain increases and BW decreases. Also,  $C_{gs}$  has no effect since it is just a capacitor in parallel with the input voltage source.(Fig. 4)

Now, if  $C_{gd}$  is included, a zero is added at  $g_m/C_{gd}$  and we see that the output voltage doesn't go to zero at very high freqs, but settles to a non-zero value depending on the relative values of  $C_{db}$  and  $C_{gd}$  .(Fig. 5)

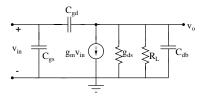


Figure 3: Small signal model at high frequencies

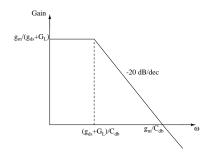


Figure 4: Gain without Cgd

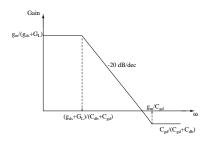


Figure 5: Gain with Cgd